A Novel Solid State Ultracapacitor

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<th>Acronym</th>
<th>Definition</th>
</tr>
</thead>
<tbody>
<tr>
<td>AC</td>
<td>alternating current</td>
</tr>
<tr>
<td>AgZn</td>
<td>silver zinc</td>
</tr>
<tr>
<td>Al₂O₃</td>
<td>alumina</td>
</tr>
<tr>
<td>ALD</td>
<td>atomic layer deposition</td>
</tr>
<tr>
<td>BaTiO₃</td>
<td>barium titanate</td>
</tr>
<tr>
<td>DC</td>
<td>direct current</td>
</tr>
<tr>
<td>DF</td>
<td>dissipation factor</td>
</tr>
<tr>
<td>EEE</td>
<td>electrical, electronic, and electromechnical</td>
</tr>
<tr>
<td>EDLC</td>
<td>electrochemical double-layer capacitor</td>
</tr>
<tr>
<td>ESR</td>
<td>equivalent series resistance</td>
</tr>
<tr>
<td>H₂</td>
<td>hydrogen gas</td>
</tr>
<tr>
<td>HESSCap</td>
<td>high energy solid state capacitor</td>
</tr>
<tr>
<td>IBLC</td>
<td>internal barrier layer capacitor</td>
</tr>
<tr>
<td>LCR</td>
<td>inductance, capacitance, resistance</td>
</tr>
<tr>
<td>Li-ion</td>
<td>lithium-ion</td>
</tr>
<tr>
<td>N₂</td>
<td>nitrogen gas</td>
</tr>
<tr>
<td>O</td>
<td>oxygen</td>
</tr>
<tr>
<td>PdAg</td>
<td>palladium silver</td>
</tr>
<tr>
<td>SEM</td>
<td>scanning electron microscopy</td>
</tr>
</tbody>
</table>
Si  silicon
SiO₂  silica
SPS  spark plasma sintering
Ti  titanium
NOMENCLATURE

$A$  surface area

$C$  capacitance

$D$  distance

$E$  energy

$e$  electron

$f$  frequency

$I$  current

$j$  imaginary part of impedance

$P$  power

$P_{\text{max}}$  maximum power

$Q$  stored charge

$R$  resistance, resistor

$t$  time

$tan \, \delta$  loss tangent delta

$V$  voltage

$V_f$  final voltage

$V_i$  initial voltage

$X$  reactance

$Z$  impedance
NOMENCLATURE (Continued)

\[ \varepsilon_0 \quad \text{vacuum permittivity} \]
\[ \varepsilon_{\text{eff}} \quad \text{effective permittivity} \]
\[ \varepsilon_r \quad \text{relative permittivity} \]
TECHNICAL MEMORANDUM

A NOVEL SOLID STATE ULTRACAPACITOR

1. INTRODUCTION

NASA analyzes, tests, packages, and fabricates electrical, electronic, and electromechanical (EEE) parts used in space vehicles. One area that NASA wishes to advance is energy storage and delivery. Currently, space vehicles use rechargeable batteries that utilize silver zinc (AgZn) or lithium ion (Li-ion) electrochemical processes. These current state-of-the-art rechargeable batteries cannot be rapidly charged, contain harmful chemicals, and suffer from early wear-out mechanisms. A solid state ultracapacitor is an EEE part that offers significant advantages over current electrochemical and electrolytic devices. The objective of this research is to develop an internal barrier layer capacitor (IBLC) using novel dielectric materials as a battery replacement with a focus on such advantages as longer life, lower mass-to-weight ratio, rapid charging, on-demand pulse power, improved on-pad standby time without maintenance, and environmental friendliness.

Ultracapacitor behavior has been reported in a number of oxides including reduced barium titanate (BaTiO$_3$) ferroelectric ceramics. BaTiO$_3$ is a ceramic material in the perovskite family that possesses a high dielectric constant. Individual coating of ferroelectric BaTiO$_3$ grains with a silica (SiO$_2$) shell followed by spark plasma sintering (SPS) in reducing conditions has been shown to lead to stable ultracapacitor behavior. The permittivity values have been reported to be $\approx 10^5$ in electroceramics.$^1$ It has also been shown that treating oxidized BaTiO$_3$ at high temperatures in reducing forming gas atmosphere (96% nitrogen gas (N$_2$), 4% hydrogen gas (H$_2$)) produces an N-type semiconducting material.$^2$ The outer coating, which remains an insulating shell, combines with this semiconducting internal layer, resulting in millions of nanocapacitors in parallel. The combination of a semiconducting grain with an insulating boundary leads to the IBLC effect.

These so-called giant ultracapacitor properties are not easily controlled. The American Piezo Ceramics International reports a relative dielectric constant of 1,550 and a dielectric dissipation factor (DF) of 0.5 for single crystal BaTiO$_3$.$^3$ High permittivity values such as relative permittivity $\varepsilon_r = 10,000$ are reported in polycrystalline ferroelectric BaTiO$_3$. Reduced BaTiO$_3$ of grain sizes between 70 and 300 nm have yielded colossal permittivity values in the order of $10^5$. The purpose of this study is to evaluate shell-coated BaTiO$_3$ processed under reducing conditions to produce the IBLC effect.
2. BACKGROUND

2.1 Conventional Capacitors

A capacitor is an electrical component consisting of two conducting electrodes separated by an insulating dielectric material. When voltage is applied across the capacitor, opposite charges accumulate on the surface of each electrode, developing a static electric field. This field causes atoms in the insulator to polarize, producing an internal electric field. Capacitors are able to store energy in this overall electric field. This is illustrated in figure 1.

![Diagram of a conventional capacitor](image)

Figure 1. Schematic of a conventional capacitor.\(^5\)

Capacitance is a measure of the ability to store charge, and it is the ratio of the stored charge \(Q\) to the applied voltage \(V\):

\[
C = \frac{Q}{V}.
\]  

(1)

The capacitance can be improved by increasing the electrode surface area \(A\) and decreasing the distance between the plates. It is also proportional to the \(\varepsilon_r\), which measures how much electric flux is generated per unit charge, and it is directly related to how easily a specific material polarizes in response to an electric field. The vacuum permittivity \(\varepsilon_0\) is a constant due to free space vacuum and
is $8.854187 \times 10^{-12}$ F/m. The relative permittivity multiplied by the vacuum permittivity is usually called the effective permittivity $\varepsilon_{\text{eff}}$:

$$C = \varepsilon_0 \varepsilon_r \frac{A}{D} \quad .$$

(2)

Capacitive loads oppose the change of voltage. Impedance $Z$ is a measure of the effect of capacitive loads. When reactance $X$ is zero, the load is purely resistive; when resistance $R$ is zero, the load is purely reactive. Ideal capacitors consist entirely of reactance, having infinite resistance:

$$Z = R + jX \quad .$$

(3)

and

$$X_C = \frac{1}{2\pi f C} \quad .$$

(4)

Loads are modeled as either series or parallel combination of a resistive and a reactive load. The parallel resistance is typically larger than the series resistance. To measure small reactive values, such as high-valued capacitors, it is preferable to use the series model because the series resistance is more significant than the parallel resistance. When measuring large reactive values, such as high-valued inductors or low-valued capacitors, it is preferable to use the parallel model. Table 1 shows the capacitance ranges and which model should be used.\textsuperscript{6}

Table 1. Model for corresponding capacitance ranges.

<table>
<thead>
<tr>
<th>Range</th>
<th>Impedance (Ω)</th>
<th>Model</th>
</tr>
</thead>
<tbody>
<tr>
<td>$&gt;100$ μF</td>
<td>&lt;10</td>
<td>Series</td>
</tr>
<tr>
<td>10 nF–100 μF</td>
<td>10–10,000</td>
<td>Series or parallel</td>
</tr>
<tr>
<td>$&lt;10$ nF</td>
<td>10,000</td>
<td>Parallel</td>
</tr>
</tbody>
</table>

At low frequencies, a capacitor is an open circuit, as no current flows in the dielectric. A direct current (DC) voltage applied across a capacitor causes positive charge to accumulate on one side and negative charge to accumulate on the other side; due to the accumulated charge, the electric field is the source of the opposition to the current. When the potential associated with the charge exactly balances the applied voltage, the current goes to zero. Driven by an alternating current (AC) supply, a capacitor will only accumulate a limited amount of charge before the potential difference changes polarity and the charge dissipates. The higher the frequency, the less charge will accumulate and the smaller the opposition to the current.\textsuperscript{7}
The two primary attributes of a capacitor for this study are its energy density and power density. The energy $E$ stored in a capacitor is directly proportional to its capacitance:

$$E = \frac{1}{2} CV^2.$$  

(5)

To determine power, capacitors are represented in series with an external load resistance $R$, shown in figure 1. The internal components of the capacitor itself contribute to the resistance as the equivalent series resistance (ESR). Maximum power $P_{\text{max}}$ for a capacitor occurs at matched impedance ($R=\text{ESR}$):

$$P_{\text{max}} = \frac{V^2}{4\times\text{ESR}}.$$  

(6)

ESR is an AC resistance dependent on frequency. In nonelectrolytic capacitors, such as electroceramics, the resistance of the leads and electrodes and losses in the dielectric cause the ESR. For a capacitor, the ESR typically falls between 0.001 and 0.1 Ω and is desired to be low. A high ESR represents increased heat dissipation, and results in accelerated aging under high temperature and large ripple current conditions. Additionally, capacitors exhibiting high ESR have a high current leakage, consuming and wasting power in the idle state, making them bad energy storage devices:

$$P = I^2 \times \text{ESR}.$$  

(7)

Electrical potential energy is dissipated in dielectric materials in the form of heat. The DF is a measure of loss-rate of energy and is proportional to the ESR. The DF is also known as loss tangent delta, $\tan \delta$, and it is represented as a percentage. This parameter depends on the dielectric material and the frequency of the electrical signals. In high dielectric constant ceramics, DF can be 1%–2%:

$$\tan \delta = \frac{\text{ESR}}{|X_C|} = \text{DF}.$$  

(8)

Dielectric $\tan \delta$ of ceramic capacitors is dependent upon specific characteristics of the dielectric formulation, level of impurities, as well as microstructural factors such as grain size, morphology, and porosity (density).

2.2 Electrochemical Double-Layer Capacitor

Conventional capacitors have relatively high-power densities but low energy densities when compared to electrochemical batteries. Stated another way, a battery may store more energy but cannot deliver it as quickly as a capacitor can. Current ultracapacitors exploit high surface area electrodes and thin dielectrics to increase both capacitance and energy. Additionally, ultracapacitors have advantages over electrochemical batteries and fuel cells, including higher power density,
shorter charging times, and longer cycle life and shelf life. The Ragone chart in figure 2 compares the power and energy densities of different types of current energy storage devices.

![Ragone chart of energy storage devices](image)

Figure 2. Ragone chart of energy storage devices. Source: Defense Logistics Agency Land and Maritime.

Electrical characteristics of ultracapacitors today lie between those of aluminum-electrolytic capacitors and fuel cells. The electrochemical double-layer capacitor (EDLC) (fig. 3) uses high surface area electrodes to elicit ultracapacitor behavior. EDLCs are constructed from two carbon-based electrodes, an electrolyte, and a separator. Ions within the electrolyte solution accumulate at the surface of the electrodes, and the separator creates a double-layer of charge. EDLCs generally operate with stable performance characteristics for many charge/discharge cycles, sometimes as many as $10^6$ cycles. On the other hand, electrochemical batteries are generally limited to only about $10^3$ cycles. Because of their cycling stability, EDLCs are well suited for applications that involve nonuser serviceable locations (e.g., deep sea and mountain environments). However, packaging paradigms for EDLCs do not permit their use in aerospace environments without hermetically sealed containers, which increase mass and volume. Currently, electrolytic ultracapacitors are used primarily in conjunction with batteries in terrestrial environments to capture sudden bursts of energy (e.g., regenerative braking systems). However, electrolytic ultracapacitors do not possess the energy density necessary to replace batteries.
2.3 Internal Barrier Layer Capacitor

A solid state ultracapacitor would overcome the limits of both the electrochemical batteries used on spacecraft and available electrochemical ultracapacitors. It provides a robust energy storage device with higher reliability and less weight and volume than electrochemical batteries and electrolytic ultracapacitors. Solid state ultracapacitors are recyclable energy storage devices that offer the promise of higher power and greater number of charge/discharge cycles than current rechargeable batteries, and they will also offer greater breakdown voltage than current electrolytic ultracapacitors. The presented research is for technology leading to a high-energy solid state capacitor (HESSCap) module to replace batteries and current state-of-the-art ultracapacitors. Table 2 presents the primary parameters for aerospace batteries and terrestrial electrolytic ultracapacitors and the target values for the HESSCap.

Table 2. Ultracapacitor/Battery comparison.

<table>
<thead>
<tr>
<th>Device</th>
<th>Energy Density (J/cc)</th>
<th>Charge/Discharge Cycles</th>
<th>Voltage (V)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Aerospace battery (Li-ion)</td>
<td>172</td>
<td>500 – 2,000</td>
<td>28</td>
</tr>
<tr>
<td>Aerospace range safety battery (AgZn)</td>
<td>57</td>
<td>&lt;12</td>
<td>28</td>
</tr>
<tr>
<td>Commercial electrolytic ultracapacitor</td>
<td>15</td>
<td>&gt;500 w/ 50% V and 25% C decrease</td>
<td>59</td>
</tr>
<tr>
<td>ES43 solid state cell (28 V)</td>
<td>80 – 200</td>
<td>&gt;500,000</td>
<td>28</td>
</tr>
</tbody>
</table>
The HESSCap module achieves high permittivity via the IBLC effect, shown in figure 4. Individual ferroelectric grains are coated by a dielectric shell followed by sintering at high temperatures and reducing forming gas atmosphere (96% N\textsubscript{2}, 4% H\textsubscript{2}). The forming gas penetrates the shell and reacts with the inner grain, making each grain semiconductive. The coating serves as an insulator, resulting in millions of nanocapacitors in parallel:

$$C_{\text{total}} = C_1 + C_2 + \ldots + C_n.$$  \hspace{1cm} (9)

The two main conditions for the internal barrier layer to increase the overall dielectric permittivity of oxides are the inner grain conductivity and the insulating grain boundary. The former is related to the amount of charged defects intentionally formed during the sintering step under reducing conditions.\textsuperscript{4} The IBLC model can be applied to any material where extended dielectric interfaces of very small thickness separate (semi)conducting parts: in ceramics, insulating grain boundaries surround conducting grains; in thin films and multilayers, surfaces and intergrowth planes can induce dielectric barriers between conducting layers.\textsuperscript{13} However, the exact nature of the conduction mechanism within the grains and of the charge accumulation at the grain boundaries is not well understood.

Figure 4. IBLC effect.
3. METHODOLOGY

3.1 Atomic Layer Deposition-Coated Ceramic Barium Titanate Nanoparticles

This study focuses on BaTiO$_3$ particles of various sizes in both coated and uncoated configurations, with the latter serving as a baseline. Table 3 provides the details on particle diameter, coating material and thickness, purity, and supplier.

<table>
<thead>
<tr>
<th>Supplier</th>
<th>Particle Size (nm)</th>
<th>Purity (%)</th>
<th>Coating</th>
<th>Thickness (nm)</th>
<th>Color</th>
</tr>
</thead>
<tbody>
<tr>
<td>Ferro</td>
<td>730</td>
<td>99.95</td>
<td>Uncoated</td>
<td>–</td>
<td>White</td>
</tr>
<tr>
<td>TPL, Inc.</td>
<td>500</td>
<td>99.95</td>
<td>SiO$_2$</td>
<td>5</td>
<td>Light grey</td>
</tr>
<tr>
<td>ALD NanoSolutions</td>
<td>500</td>
<td>99.95</td>
<td>Alumina</td>
<td>10</td>
<td>White</td>
</tr>
</tbody>
</table>

The BaTiO$_3$ particles used in this study varied in median diameter, also known as particle size distribution D50, ranging from 500 to 730 nm. Coating configurations varied from uncoated to 10 nm. The uncoated BaTiO$_3$ sample was a fine powder, while the coated BaTiO$_3$ samples had agglomerated powder. The clumps are likely caused by hydrophilic interaction or static charge. The clumps were dispersed before processing using ink formulations.

Atomic layer deposition (ALD) was used to deposit nano-thin films over BaTiO$_3$ nanoparticles. ALD is based on the sequential use of a proprietary gas phase chemical process. The nano-thin film coatings consist of 10 nm alumina (Al$_2$O$_3$) and 5 nm SiO$_2$. Figure 5 shows a transmission electron microscope image of a coated BaTiO$_3$ particle used in this study. The number of cycles achieved during ALD determines the coating thickness. The coating thickness rate for Al$_2$O$_3$ was 10 Å per cycle and for SiO$_2$ was 4 Å per cycle. It is important to note that previous IBLC research using SPS of BaTiO$_3$ particles were coated by the Stöber process, a method based on a seeded growth process.$^{1,14}$ The Stöber process is known to produce an inconsistent coating.
SiO$_2$-coated BaTiO$_3$ becomes oxygen deficient and semiconductive under vacuum sintering condition, turning the coating layer into an isolating insulator layer.$^1$ It was thought that the structure became that of the internal barrier layer semiconductor ceramics. However, the location of SiO$_2$ determined by a silicon (Si) elemental mapping of disk cross section by scanning transmission electron microscopy-energy divergent spectroscopy (STEM-EDS) detects almost no Si elements in the grain boundary of BaTiO$_3$; instead, it is segregated. This implies that Si plays no important role of insulation because it cannot stay on the surface of grains. Rather, it diffuses during the sintering process.$^{15}$ Some testing performed at Auburn University suggests the opposite; namely, there does appear to be SiO$_2$ remaining on the surface grains. Whatever the interaction between semiconducting BaTiO$_3$ and its coating may be, the colossal permittivity values cannot be ignored, so this coating was kept under consideration for this investigation.

### 3.2 High-Temperature and Reduced Forming Gas Sintering

In reducing atmospheres (96% N$_2$, 4% H$_2$), BaTiO$_3$ is slightly reduced, forming doubly ionized oxygen (anion) vacancies. This produces the same effect as vacuum sintering, so a reducing atmosphere was the preferred method of processing. To understand vacancy creation, a BaTiO$_3$ crystal structure is shown in figure 6. The conductivity results from the electron exchange between Ti$^{+4}$ and Ti$^{+3}$ because oxygen vacancies are created at the octahedron.$^2$ The induced free electrons make the reduced perovskite material highly semiconducting. Sintering BaTiO$_3$-based dielectrics in forming gas decreases the insulation resistance (IR) by 10–12 orders of magnitude$^{16}$:

$$\text{BaTiO}_3 + x\text{H}_2 \rightarrow \text{BaTiO}_{3-x}[V_O]_x + x\text{H}_2\text{O}$$  \hspace{1cm} (10)

and

$$[V_O] \rightarrow [V_O]^{\text{+2}e}.$$  \hspace{1cm} (11)
Figure 6. The BaTiO$_3$ crystal structure. The green, red, and blue atoms are titanium, oxygen, and barium, respectively. Source: <www.crystalmaker.com>.

A three-zone Thermo Scientific™ Lindberg Blue™ tube furnace was used to process the particles. The furnace was heated uniformly to 300 °C, left to hold for an hour to avoid thermal shock of the quartz tube, and then set to the desired temperature ranging from 500 °C to 1,100 °C. The duration varied from 1 to 30 hr. Three quartz boats were each filled with 5 g of Al$_2$O$_3$-coated, SiO$_2$-coated, and uncoated BaTiO$_3$. The uncoated BaTiO$_3$, serving as a baseline, was always heat treated to evaluate its electrical properties versus those of coated particles. The forming gas was turned on at 3 SCFH for 10 min prior to placing the samples inside. After the desired annealing duration, the furnace was set to cool to 300 °C with the forming gas flowing to avoid any reoxidation of the samples while exposed to high temperatures. The furnace was then opened and observations were made on the color of the samples inside the tube furnace. Finally, the forming gas was turned off and the samples were left to cool to room temperature inside the tube furnace before removal.

Previous studies show that the reduction of BaTiO$_3$ in H$_2$ at intermediate temperatures (500 °C) leads to bodies of bright yellow color.$^{17}$ Significantly reduced SiO$_2$-coated material obtained through SPS at a final temperature of 1,110 °C is expected to change from white to a navy blue color.$^3$ Uncoated BaTiO$_3$ and doped BaTiO$_3$ specimens that show a remarkable reduction in resistivity have also been characterized with a bluish color.$^{18}$ To assess color changes, optical microscopy images of the pellets were taken at 7× magnification.

When powdered particles are heated to a high temperature below the melting point, the atoms in the powder diffuse across the particle boundaries fusing the particles together. Two additive manufacturing techniques used for electrode and dielectric deposition, such as aerosol jet
deposition and screen printing, require unfused particles in order to deposit the material properly. In order to screen print the particles, they were separated using a three-roll mill.

### 3.3 Pellet Electrical Characterization

The unsintered powders were pressed into pellets, without the addition of binder, using a potassium bromide die. A literature review revealed that pellets pressed at pressures above 50,000 psi could not be recovered. Various pressures were tested revealing that pellets pressed at forces above 400 lb could not be recovered from the potassium bromide die in suitable shape. Because of these findings, the pellets were pressed at 300 lbf using a TestResources, Inc., compression and tension machine. The pellets were 4–8 mm thick with masses of 1.5–2.5 g.

The adsorption of water vapor increases the permittivity by a factor of two. However, the focus of the characterization at this phase of the study was to identify a sample with a large change in permittivity, specifically by a factor of $10^4$. Because the focus was large changes in permittivity, no attempt was made to remove the water. In addition, thin film electrical characterization is used to obtain the most accurate measurements, and since the thin films undergo sintering, the water absorption effects are eliminated.

Capacitance, DF, and ESR were measured for a frequency range of 20 Hz to 2 MHz using a Dielectric Test Fixture 1645-1B together with an Agilent E4980A precision inductance, capacitance, and resistance (LCR) meter, shown in figure 7. The capacitance was initially assumed small; therefore, measurements were made using the LCR meter’s parallel model. If the values were found to be higher than expected, then the instrument could be reset to use a series model for accuracy. The dielectric constant of the samples was determined from the instrument’s reported capacitance value. No porosity correction was made to the dielectric constant.

![Image of Dielectric Test Fixture 1645-1B and Agilent E4980A precision LCR meter](image-url)
3.4 Dielectric Ink Formulation

To perform 3D additive manufacturing, the powders were first converted into an ink. The formulation for this ink is shown in table 4. Glass particulates were used to increase densification, but high quantities of glass particles decrease the permittivity, so the concentration of glass was kept as low as possible to produce a usable ink. Surfactant was used as a wetting agent to allow the ink to spread. A thinner was also used to obtain the proper ink viscosity. Texanol was used as a thinner because it volatilizes at 120 °C. The vehicle was an organic binder formulated from a blend of Ashland Chemical Ethyl Cellulose N200 in Texanol, and it was used to further enhance the viscosity of the ink. The vehicle was chosen because it volatilizes between 250 °C and 350 °C during sintering.

Table 4. Dielectric ink formulation.

<table>
<thead>
<tr>
<th>Component</th>
<th>Concentration (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>BaTiO₃ dielectric</td>
<td>72.5</td>
</tr>
<tr>
<td>Lead-germinate high K glass</td>
<td>7.5</td>
</tr>
<tr>
<td>Surfactant (wetting agent)</td>
<td>0.5</td>
</tr>
<tr>
<td>Texanol (solvent)</td>
<td>5</td>
</tr>
<tr>
<td>Ethyl cellulose organic vehicle</td>
<td>15</td>
</tr>
</tbody>
</table>

The dielectric ink formulation was mixed and then ground in a three-roll mill. A three-roll mill is a tool that uses shear force from three horizontally positioned rolls rotating at opposite directions and different speeds relative to each other to mix, refine, disperse, and homogenize viscous materials fed into it. The final ink was a dense, homogenous mixture used for screen printing.

3.5 3D Additive Thick Film Deposition

The screen printing method was the chosen method of printing a test cell for this study. This technique can produce layers as thin as 5 µm. By producing such a thin dielectric layer, the capacitance relationship (eq. 2) shows that the energy stored can be increased significantly. The screen printing process began by creating a design on a woven mesh using photolithography. The ink was forced into the mesh openings by a squeegee and onto the printing surface during the squeegee stroke. The larger the number of intertwined meshes, the thinner the deposition becomes for a single stroke. The capacitor layers (fig. 8) were printed using a Hary Manufacturing, Inc. 485 precision screen printer. Palladium silver (PdAg) ink that is used in multilayer chip capacitors due to its conductance and resistance to silver migration was used as the electrode material. Al₂O₃ (0.039 in, 96% purity) was used as the substrate on which each layer was deposited. Al₂O₃ was chosen because it has a very low coefficient of expansion and will not impart excessive stress during later sintering steps. As a result, each layer is only able to densify in the axis perpendicular to the substrate, due to clamping to the substrate. The ultracapacitor test cells were made using two layers of dielectric applied through 325 and 400 mesh screens, respectively.
Figure 8. Top and side view of the ultracapacitor module layers.

The capacitor test cell was sintered, using an HSA1505-0811Z belt furnace from Hengli Eletek Company, at 850 °C peak for 10 min, and a total cycle time of 1.5 hr. This sintering step was performed after each layer deposition in order to burn off organic materials and achieve high densification. The temperature settings of the eight-zone belt furnace are shown in figure 9, the temperature profile in figure 10, and the nitrogen flow profile in table 5. Previous work shows that when reduced SiO$_2$-coated BaTiO$_3$ is post-annealed at 800 °C for 12 hr in air, it remains blue, while reduced uncoated BaTiO$_3$ turns white.$^{13}$ For this reason, the SiO$_2$ shell was thought to act as an efficient barrier against oxidation. As a further preventative measure, the belt muffle furnace was purged with nitrogen to avoid reoxidation. Densification of the dielectric layer was then evaluated with the scanning electron microscope (SEM).

Figure 9. Eight-zone belt furnace temperature settings.
3.6 Thick Film Electrical Characterization

The ultracapacitor test cell was measured for parallel capacitance using the LCR meter. Capacitance readings were then used to determine if the device was functional. When readings were found to be unstable, due to either shorted electrodes or low ESR values, the capacitance was measured using the discharge method. To use the discharge method, the capacitor was discharged through a resistor determined to yield a reasonable time constant. The voltage versus time plot was captured with a DPI5104 digital phosphor oscilloscope. A large region of the discharge curve was chosen, and the values of voltage in the discharge cycle and time required to drop between the two voltages were entered into equation (12) along with the known resistor value. In this equation, \( t \) is the time it takes to discharge the capacitor between some initial voltage \( V_i \) to some final voltage \( V_f \); \( C \) is the capacitance to be determined, and \( R \) is a resistor through which the capacitor is discharged:

\[
t = C \times R \times \ln\left(\frac{V_C}{V_i}\right).
\]

(12)
4. ANALYSIS

4.1 Pellet Electrical Characterization

SEM images of the untreated powders (figs. 11(a) and (b)) revealed that particles indicated by the manufacturer to be 500 nm actually varied in diameter from 250 nm up to 1 µm. Treated powders (fig. 11(c)) also showed varying particle sizes of the same range. These observations showed that the furnace treatment was not causing grain growth.

Figure 11. SEM images of BaTiO$_3$ (a) uncoated from TPL, (b) coated with Al$_2$O$_3$, and (c) Al$_2$O$_3$-coated treated at 750 °C for 30 hr.

All three configurations of powder batches were initially white in color, as can be seen in figure 12. When treated at temperatures below 900 °C, they turned to a bright yellow or neon green color. These powders remained that color under the reduced forming gas atmosphere and changed to white after the first minute of exposure to air. Scraping off the top layer of the treated powder revealed two shades of color, a lighter tone on top and a darker tone underneath. This nonuniform color, shown in figures 13 and 14, indicates that the particles were not being sintered homogeneously.

Figure 12. Optical microscopy photographs of untreated (a) uncoated, (b) SiO$_2$-coated, and (c) Al$_2$O$_3$-coated BaTiO$_3$ pellets.
Figure 13. Optical microscopy photographs of (a) uncoated, (b) SiO$_2$-coated, and (c) Al$_2$O$_3$-coated BaTiO$_3$ pellets treated at 900 °C for 1 hr.

Figure 14. Optical microscopy photographs of (a) uncoated, (b) SiO$_2$-coated, and (c) Al$_2$O$_3$-coated BaTiO$_3$ pellets treated at 1,100 °C for 1 hr.

At temperatures below 900 °C, no significant changes are seen in the permittivity. At temperatures above 900 °C, the permittivity and DF slightly increased for uncoated BaTiO$_3$ and decreased for coated samples. The ESR decreased only for the Al$_2$O$_3$-coated sample, the greatest decrease occurring with 900 °C treatment. The decrease in ESR coincides with the color change (fig. 15) which can be interpreted as the material undergoing reduction.
Figure 15. Plots of (a) permittivity, (b) DF, and (c) ESR samples treated at 900 °C for 15 hr and 1,100 °C for 1 hr compared to the untreated powders.
The synthesis profile that produced the maximum increase in permittivity for all samples was at 900 °C for 1 hr. Table 6 shows the effect of a short-duration treatment versus a long-duration treatment with constant (900 °C) temperature. The SiO₂-coated sample exhibits the highest permittivity.

Table 6. Synthesis profile effect on dielectric permittivity.

<table>
<thead>
<tr>
<th>BaTiO₃ at 20 Hz</th>
<th>Untreated</th>
<th>1 Hour at 900 °C</th>
<th>15 Hours at 900 °C</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>Color</td>
<td>Permittivity</td>
<td>Color</td>
</tr>
<tr>
<td>Uncoated</td>
<td>White</td>
<td>9</td>
<td>White</td>
</tr>
<tr>
<td>Al₂O₃-coated</td>
<td>White</td>
<td>217</td>
<td>Light blue</td>
</tr>
<tr>
<td>SiO₂-coated</td>
<td>White</td>
<td>7,638</td>
<td>Grey</td>
</tr>
</tbody>
</table>

The capacitor properties versus frequency of the samples treated at 900 °C for 1 hr are compared in figure 16. Low-frequency permittivities are high (maximum 19,980 at 20 Hz), indicating the dielectric may useful for DC applications. The DF was found to increase with treatment, and it is likely that further sintering will decrease the rate of energy loss. The decreased ESR for all treated powders indicates that they are becoming semiconducting, one of the desired outcomes for the IBLC effect. SiO₂-coated and Al₂O₃-coated BaTiO₃ treated at 900 °C for 1 hr were chosen as the dielectric for the capacitor test cell because of the best capacitance traits.
Figure 16. Plots of (a) permittivity, (b) DF, and (c) ESR samples treated at 900 °C for 1 hr compared to the untreated powders.
4.2 Thick Film Electrical Characterization

The color of the dielectric ink made up of $\text{Al}_2\text{O}_3$ and $\text{SiO}_2$ were initially light blue and grey, respectively. After deposition on the substrate followed by sintering, both changed color to snow white, a much whiter tone than observed in the untreated powders. Figure 17 shows an ultracapacitor test cell made with $\text{SiO}_2$-coated $\text{BaTiO}_3$.

![Ultracapacitor test cell made from $\text{SiO}_2$-coated $\text{BaTiO}_3$ deposited by screen printing.](image)

Figure 17. Ultracapacitor test cell made from $\text{SiO}_2$-coated $\text{BaTiO}_3$ deposited by screen printing.

Experiments were run to test for oxidation. A copper coupon and treated powders were sintered in the belt furnace. The copper became grey in color, which indicated that the copper had oxidized. Likewise, the treated powders also changed in color back to white. Measurements taken on the sintered powders (fig. 18) displayed a decrease in permittivity and $\text{DF}$, and an increase in $\text{ESR}$. The data trend indicates oxidation, and suggests that there was an oxygen leak inside the Nitrogen-purged belt furnace. This was undesirable, and adjustments were made to lower the oxygen parts per million.
Figure 18. Plots of (a) permittivity, (b) DF, and (c) ESR powdered samples treated at 900 °C for 1 hr before and after furnace sintering.
SEM images (fig. 19) on the ultracapacitor test cells showed a 70% to 80% densification. The thickness for samples built using the 325 mesh was an average of 20 µm. Five out of 15 test cells had normal capacitor characteristics; the remaining (three SiO$_2$ and the rest Al$_2$O$_3$) were shorted.

Figure 19. SEM image showing a 75% densification and the porosity of SiO$_2$-coated BaTiO$_3$ test cell with 184 nF of capacitance.
Table 7 shows the capacitor test cells built and their measured electrical characteristics. The thinnest capacitor was 13.5 µm. When tested at 50 V, the energy density was found to be $7.96 \times 10^{-2}$ J/cc, and a capacitance of 125 nF at 1 kHz. The capacitance obtained through the discharge method using a DC source agrees with the capacitance values within ±5%. The voltage versus time plot for the 184.2 nF capacitor is shown in figure 20. If these devices can withstand 500 V, then one can expect $100 \times$ the energy storage, or about 8 J/cc. The voltage breakdown plot in figure 21 shows that some devices do withstand voltages exceeding 500 V.

<table>
<thead>
<tr>
<th>Mesh</th>
<th>Capacitance (nF) at 1 kHz</th>
<th>Thickness (µm)</th>
<th>Electrode Area (mm²)</th>
<th>Porosity (%)</th>
<th>Test Voltage (V)</th>
<th>Energy Density at Test Voltage (J/cc)</th>
</tr>
</thead>
<tbody>
<tr>
<td>400</td>
<td>184.20</td>
<td>8.40</td>
<td>141.29</td>
<td>75</td>
<td>13</td>
<td>$1.31 \times 10^{-2}$</td>
</tr>
<tr>
<td>400</td>
<td>73.34</td>
<td>111.90</td>
<td>146.32</td>
<td>70</td>
<td>25</td>
<td>$0.14 \times 10^{-2}$</td>
</tr>
<tr>
<td>325</td>
<td>125.00</td>
<td>13.50</td>
<td>145.46</td>
<td>75</td>
<td>50</td>
<td>$7.96 \times 10^{-2}$</td>
</tr>
<tr>
<td>325</td>
<td>125.00</td>
<td>24.73</td>
<td>141.24</td>
<td>75</td>
<td>25</td>
<td>$1.12 \times 10^{-2}$</td>
</tr>
<tr>
<td>325</td>
<td>130.00</td>
<td>22.20</td>
<td>144.10</td>
<td>80</td>
<td>45</td>
<td>$4.11 \times 10^{-2}$</td>
</tr>
</tbody>
</table>

Table 7. SiO₂-coated BaTiO₃ capacitor test cell characteristics.

Figure 20. Voltage versus time plot used for the discharge method.
Figure 21. Breakdown curves for a device exhibiting breakdown >500 V.

Electrical characterization (fig. 22) shows normal capacitor behavior up to 1.3 MHz. Above the latter frequency, the capacitor test cells exhibit a negative capacitance and DF that spikes up to $3 \times 10^3$. This negative capacitance effect is observed in a variety of semiconductor devices.
Figure 22. Plots of (a) capacitance, (b) DF, and (c) ESR capacitor test cells, made from the dielectric material treated at 900 °C for 1 hr before and after furnace sintering.


5. CONCLUSIONS

A material and set of processing conditions were selected that give the optimal properties for fabricating a device. The material of choice, SiO$_2$-coated BaTiO$_3$, exhibited the highest dielectric permittivity. This particular sample was treated at 900 °C for 1 hr. The processed material exhibited the following properties at 20 Hz: permittivity of 19,980, DF of 215%, and an ESR of 806 kΩ. A test cell was built with the selected material at a thickness of 13.5 μm, and it exhibited a capacitance of 125 nF at 1 kHz and an energy density of $7.96 \times 10^{-2}$ J/cc at 50 V. The data indicate that the BaTiO$_3$, although properly reduced in the powder form, was subsequently oxidized due to an oxygen leak in the belt furnace when sintered in device form. Despite oxidizing the sample, the initial indications are that even in an oxidized state, the potential for large energy storage, especially at higher voltages, is possible.

Treatment at temperatures below 900 °C did not significantly affect the dielectric properties of the material. The decrease in properties for samples treated above 900 °C may be attributed to an overreduction or to excess interdiffusion. Though it did not experience a color change, SiO$_2$ obtained the highest initial and after-treatment permittivity. The color tone difference within a powder batch after being reduced indicates that a better sealed tube furnace or other synthesis techniques are necessary to obtain a homogeneous treatment.

The test cells’ low densification (70%) must be improved. For better densification and characterization, a new technique will be developed. Densification can be increased while decreasing the thickness using other thin film deposition techniques such as aerosol jet deposition. For screen printing, a triple layer of dielectric material will be necessary to avoid shorted samples.

Finally, further study involving transmission electron microscopy and x-ray photoelectron spectroscopy are necessary to identify whether the ALD coating remains on the particles after synthesis and ink formulation, and to determine the role the coating plays in BaTiO$_3$ reduction. After ultracapacitor test cells are built, several of them will be connected in parallel (fig. 23), packaged (fig. 24), and tested for use in aerospace applications and common electronic devices.
Figure 23. Ultracapacitor cells in parallel.

Figure 24. Ultracapacitor package.
REFERENCES


A Novel Solid State Ultracapacitor


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National Aeronautics and Space Administration
Washington, DC 20546–0001

Novel dielectric materials were researched to develop an internal barrier layer capacitor that is fully solid state. These materials included reduced nanoparticles of barium titanate that were coated with various atomic layer deposited oxides. The nanoparticle powders were then densified into pellets and characterized using a dielectric test fixture over a frequency range of 20 Hz to 2 MHz. Densification and sintering were evaluated using scanning electron microscopic techniques. Ultimately, the samples showing the most promising electrical characteristics of permittivity, dissipation factor and equivalent series resistance were chosen to manufacture devices for subsequent testing.
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